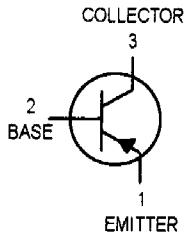


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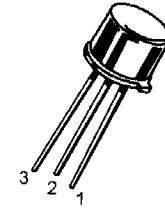
General Purpose Transistors PNP Silicon



**2N4036
2N4037**

MAXIMUM RATINGS

Rating	Symbol	2N4036	2N4037	Unit
Collector-Emitter Voltage	V_{CEO}	-65	-40	Vdc
Collector-Base Voltage	V_{CBO}	-90	-60	Vdc
Emitter-Base Voltage	V_{EBO}	-7.0	-7.0	Vdc
Base Current	I_B	-0.5		Adc
Collector Current — Continuous	I_C	-1.0		Adc
Continuous Power Dissipation at or Below $T_C = 25^\circ\text{C}$ Linear Derating Factor	P_D	5.0 28.6	5.0 28.6	Watts mW/ $^\circ\text{C}$
Continuous Power Dissipation at or Below $T_A = 25^\circ\text{C}$ Linear Derating Factor	P_D	1.0 5.72	1.0 5.72	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		$^\circ\text{C}$
Lead Temperature 1/16" from Case for 10 Seconds	T_L	230		$^\circ\text{C}$



TO-39 (TO-205AD)

THERMAL CHARACTERISTICS

Characteristic	Symbol	2N4036	2N4037	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	35	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage(1) ($I_C = -100 \mu\text{A}$, $I_B = 0$)	$V_{CEO}(\text{sus})$	-65 -40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = -0.1 \mu\text{A}$)	$V_{(BR)CBO}$	-60	—	Vdc
Collector Cutoff Current ($V_{CE} = -85 \text{ Vdc}$, $V_{EB} = -1.5 \text{ Vdc}$) ($V_{CE} = -30 \text{ Vdc}$, $V_{EB} = -1.5 \text{ Vdc}$, $T_C = 150^\circ\text{C}$)	I_{CEX}	— —	-0.1 -100	μA
Collector Cutoff Current ($V_{CB} = -90 \text{ Vdc}$, $I_E = 0$) ($V_{CB} = -60 \text{ Vdc}$, $I_E = 0$)	I_{CBO}	— —	-1.0 -0.25	μA
Emitter Cutoff Current ($V_{EB} = -7.0 \text{ Vdc}$, $I_C = 0$) ($V_{EB} = -5.0 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	— —	-10 -1.0	μA

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.



2N4036 2N4037

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit
ON CHARACTERISTICS					
DC Current Gain ($I_C = -0.1 \text{ mA}_\text{dc}$, $V_{CE} = -10 \text{ V}_\text{dc}$)	2N4036	h_{FE}	20	—	—
($I_C = -1.0 \text{ mA}_\text{dc}$, $V_{CE} = -10 \text{ V}_\text{dc}$)	2N4037		15	—	—
($I_C = -150 \text{ mA}_\text{dc}$, $V_{CE} = -10 \text{ V}_\text{dc}$) ⁽¹⁾	2N4036		40	140	—
	2N4037		50	250	—
($I_C = -150 \text{ mA}_\text{dc}$, $V_{CE} = -2.0 \text{ V}_\text{dc}$) ⁽¹⁾	2N4036		20	200	—
($I_C = -500 \text{ mA}_\text{dc}$, $V_{CE} = -10 \text{ V}_\text{dc}$) ⁽¹⁾	2N4036		20	—	—
Collector-Emitter Saturation Voltage ⁽¹⁾ ($I_C = -150 \text{ mA}_\text{dc}$, $I_B = -15 \text{ mA}_\text{dc}$)	2N4036 2N4037	$V_{CE(\text{sat})}$	— —	-0.65 -1.4	V_dc
Base-Emitter Saturation Voltage ⁽¹⁾ ($I_C = -150 \text{ mA}_\text{dc}$, $I_B = -15 \text{ mA}_\text{dc}$)	2N4036	$V_{BE(\text{sat})}$	—	-1.4	V_dc
Base-Emitter On Voltage ⁽¹⁾ ($I_C = -150 \text{ mA}_\text{dc}$, $V_{CE} = -10 \text{ V}_\text{dc}$)	2N4037	$V_{BE(\text{on})}$	—	-1.5	V_dc

SMALL-SIGNAL CHARACTERISTICS

Collector-Base Capacitance ($V_{CB} = -10 \text{ V}_\text{dc}$, $f = 1.0 \text{ MHz}$)	2N4037	C_{cb}	—	30	pF
Current Gain — High Frequency ($I_C = -50 \text{ mA}_\text{dc}$, $V_{CE} = -10 \text{ V}_\text{dc}$, $f = 20 \text{ MHz}$)	2N4036 2N4037	$ h_{fe} $	3.0 3.0	— 10	—

SWITCHING CHARACTERISTICS

Rise Time ($I_{B1} = -15 \text{ mA}_\text{dc}$)	2N4036	t_r	—	70	ns
Storage Time ($I_{B2} = -15 \text{ mA}_\text{dc}$)	2N4036	t_s	—	600	ns
Fall Time ($I_{B2} = -15 \text{ mA}_\text{dc}$)	2N4036	t_f	—	100	ns
Turn-On Time ($I_{B1} = I_{B2}$)	2N4036	t_{on}	—	110	ns
Turn-Off Time ($I_{B1} = I_{B2}$)	2N4036	t_{off}	—	700	ns

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.